Form PTO-1449 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 119498	APPLICATION NO. 10/826,354
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	APPLICANT Hiromi OTOMA	EX: CHUC TRAN
	FILING DATE April 19, 2004	GROUP ~~2828~~ 2821

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
CT	1.	JP A 2002-185079 w/abstract & transl.	6/28/2002	JAPAN		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

CT	2.	Kenichi IGA; "Surface Emitting Laser"; IEICE Transactions C-1, Vol. J81-C-1, No. 9; September 1998; pp 483-493
	3.	H. OTOMA et al.; "Fabrication and Performance of 12 X 12 Matrix-Addressed 780nm Oxide-Confined Vcsel Array"; Bulletin of Solid State Physics and Applications; Vol. 5, No. 1.; 1999; pp 11-15
CT	4.	Nobuaki UEKI et al.; "Single-Transverse-Mode 3.4-mW Emission of Oxide-confined 780-nm Vcsel's"; IEEE Photonics Technology Letters; Vol. 11, No. 12; December 1999; pp 1539-1541
	5.	Jun SAKURAI et al.; "10 Gb/s Surface Emission Semiconductor Laser"; Electronic Materials, Vol. 41, No. 11; November 2002; pp 49-52
CT	6.	M. Grabherr et al.; "Efficient Single-Mode Oxide-Confined GaAs VCSEL's Emitting in the 850-nm Wavelength Regime"; IEEE Photonics Technology Letters; Vol. 9, No. 10, ; October 1997; pp 1304-1306
	7.	Aaron et al.; "Aperture Placement Effects in Oxide-Defined Vertical-Cavity Surface-Emitting Lasers"; IEEE Photonics Technology Letters; Vol. 10, No. 10; October 1998; pp 1362-1364

EXAMINER /Chuc Tran/	DATE CONSIDERED 05/15/2006

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: July 29, 2004